

# ACMS93P04H8-HF

P-Channel  
RoHS Device  
Halogen Free



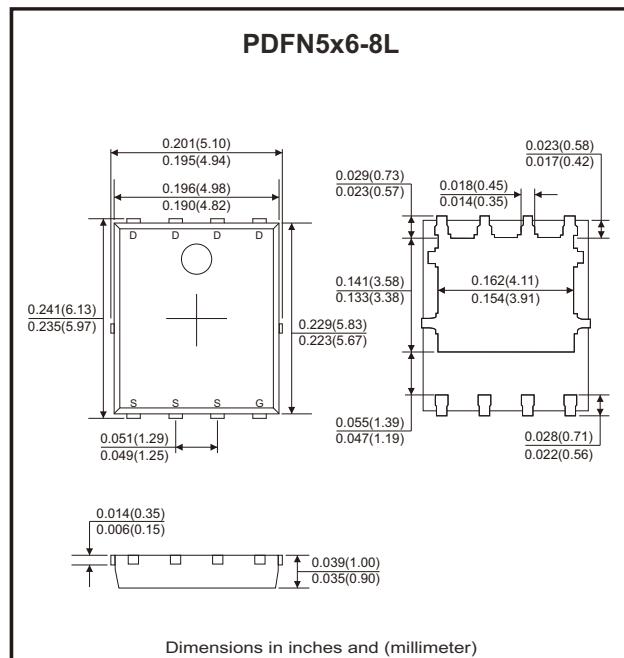
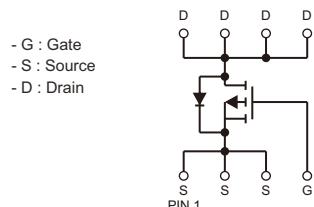
## Features

- Advanced trench technology.
- Super low on-resistance.
- Fast switching speed.
- AEC-Q101 Qualified.

## Mechanical data

- Case: PDFN5x6-8L, molded plastic.
- Terminals: Matte tin-plated leads, solderability-per MIL-STD-202, method 208.
- Mounting position: Any.

## Circuit Diagram



## Maximum Ratings (at $T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	-40	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current ( $T_c=25^\circ\text{C}$ )	$I_D$	-93	A
Continuous drain current ( $T_c=100^\circ\text{C}$ )	$I_D$	-59	
Continuous drain current ( $T_A=25^\circ\text{C}$ ) (Note 1)	$I_D$	-16	
Continuous drain current ( $T_A=100^\circ\text{C}$ ) (Note 1)	$I_D$	-10	
Pulsed drain current ( $t_p=10\mu\text{s}$ , $T_c=25^\circ\text{C}$ )	$I_{DM}$	-372	A
Single pulse avalanche energy (Note 3)	$E_{AS}$	230	mJ
Power dissipation ( $T_c=25^\circ\text{C}$ )	$P_D$	96	W
Operating junction temperature range	$T_J$	-55 to +150	°C
Storage temperature range	$T_{STG}$	-55 to +150	°C

## Thermal Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Thermal resistance junction to case	$R_{\theta JC}$		0.8	1.3	°C/W
Thermal resistance junction to air (Note 1)	$R_{\theta JA}$		26	40	°C/W

## Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-40			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>On Characteristics</b>						
Static drain-source on-resistance (Note 2)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -20A		4.7	6.5	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A		6.3	9	mΩ
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.7	-2.5	V
Gate resistance	R <sub>G</sub>	V <sub>GS</sub> = 0V, f = 1MHz		2.9		Ω
<b>Dynamic Characteristics</b>						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V, f = 100kHz		6237		pF
Output capacitance	C <sub>oss</sub>			472		
Reverse transfer capacitance	C <sub>rss</sub>			426		
<b>Switching Characteristics</b>						
Turn-on delay time (Note 4)	t <sub>d(on)</sub>	V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 3Ω I <sub>D</sub> = -20A		16		ns
Turn-on rise time (Note 4)	t <sub>r</sub>			17		
Turn-off delay time (Note 4)	t <sub>d(off)</sub>			68		
Turn-off fall time (Note 4)	t <sub>f</sub>			31		
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -20A		125		nC
Gate to source charge	Q <sub>gs</sub>			15.3		
Gate to drain (miller) charge	Q <sub>gd</sub>			23.2		
<b>Source-Drain Diode Characteristics</b>						
Diode forward voltage (Note 2)	V <sub>SD</sub>	I <sub>SD</sub> = -20A, V <sub>GS</sub> = 0V		-0.8	-1.2	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -20A, V <sub>GS</sub> = 0V, dI <sub>F</sub> /dt = 100A/μs		61		ns
Reverse recovery charge	Q <sub>rr</sub>			52		nC

Notes: 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
3. The EAS data shows max. rating. The test condition is V<sub>DD</sub>= -30V, V<sub>GS</sub>= -10V, L=0.5mH.
4. Guaranteed by design, not subject to production.

## Typical Rating and Characteristic Curves (ACMS93P04H8-HF)

Fig.1 - Power Dissipation

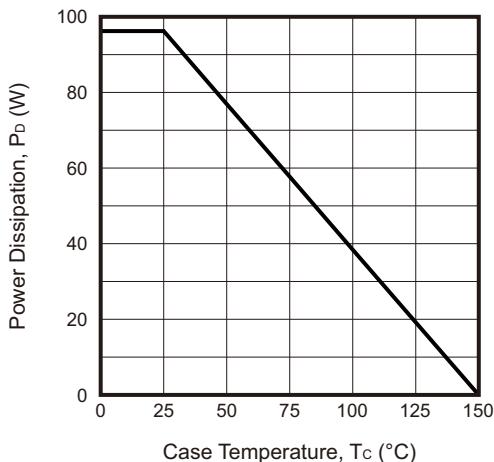


Fig.2 - Drain Current

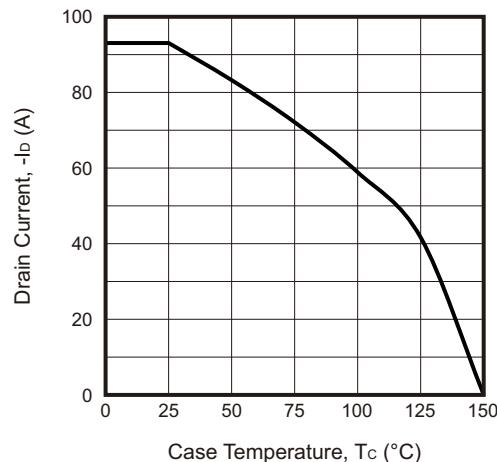


Fig.3 - Typical Output Characteristics

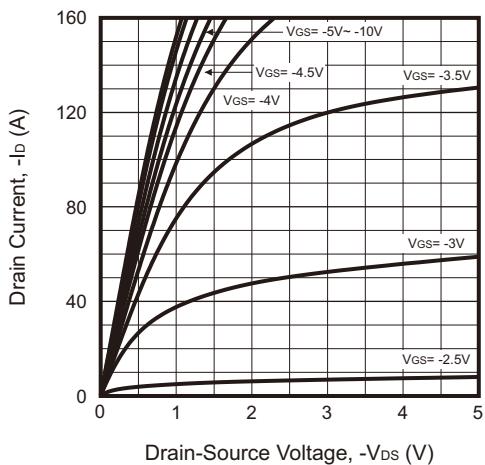


Fig.4 - On-Resistance vs.  
Drain Current and Gate Voltage

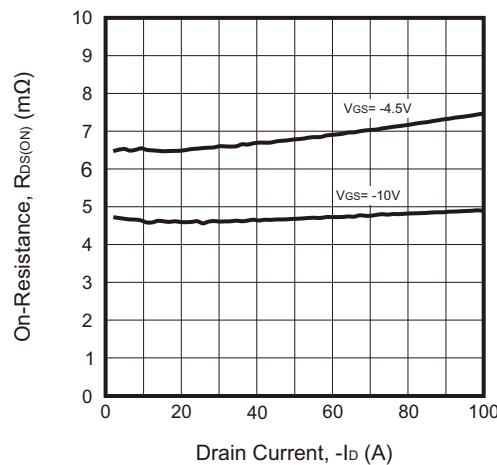


Fig.5 - On-Resistance vs. Gate-Source Voltage

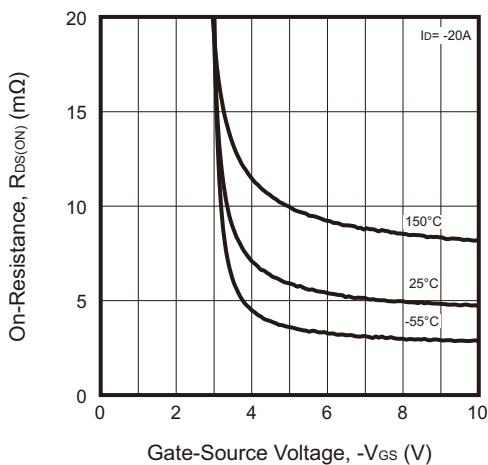
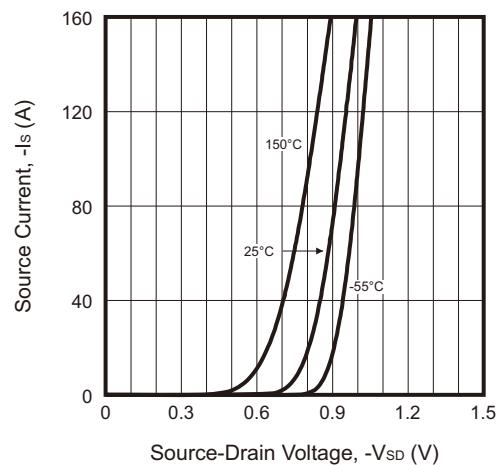


Fig.6 - Body-Diode Characteristics



## Typical Rating and Characteristic Curves (ACMS93P04H8-HF)

Fig.7 - Normalized On-Resistance vs. Junction Temperature

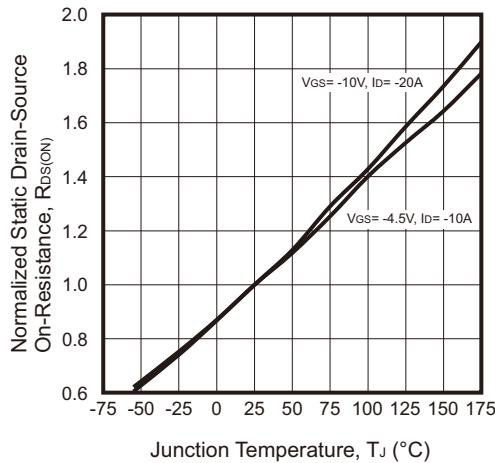


Fig.8 - Transfer Characteristics

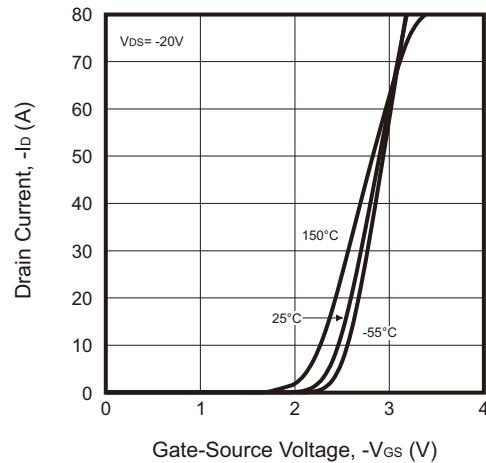


Fig.9 - Capacitance Characteristics

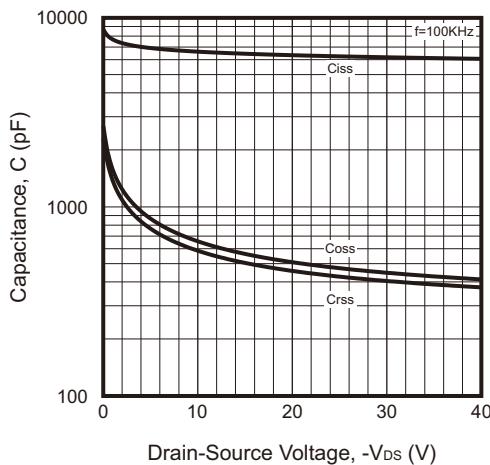


Fig.10 - Gate Charge Characteristics

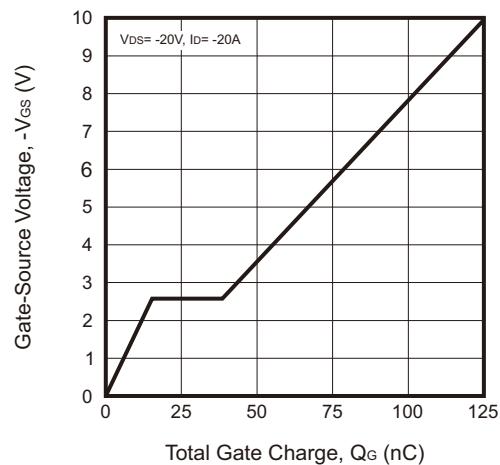


Fig.11 - Normalized Breakdown Voltage vs. Junction Temperature

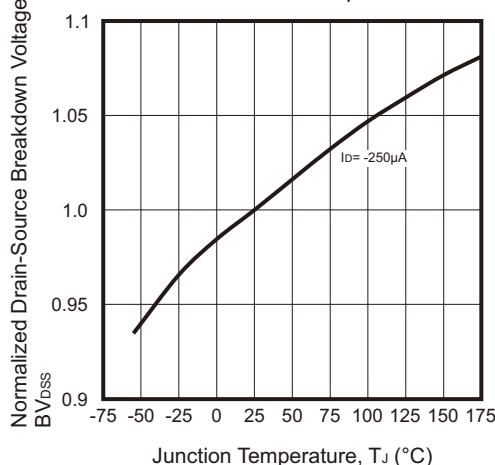
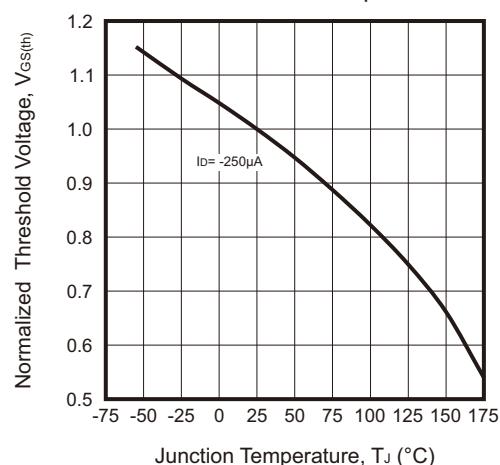
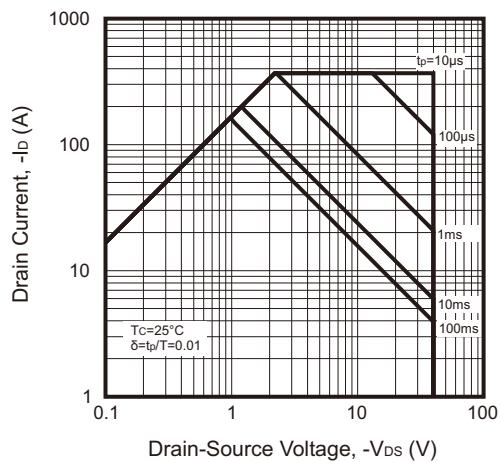


Fig.12 - Normalized  $V_{GS(th)}$  vs. Junction Temperature

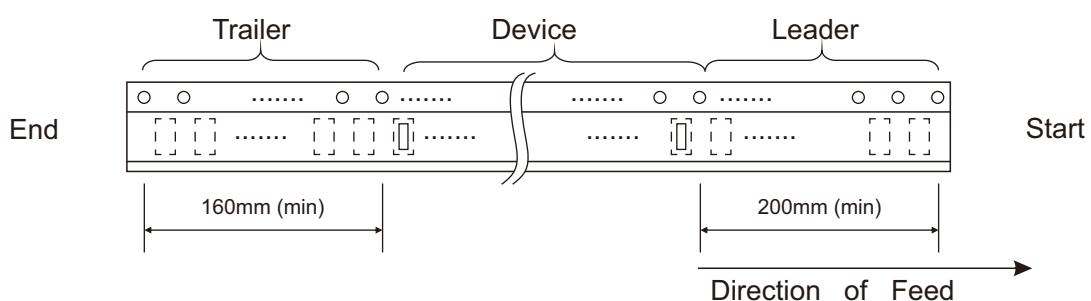
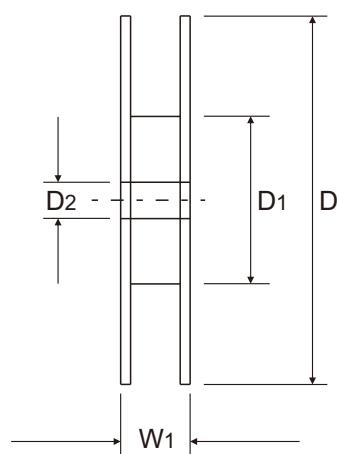
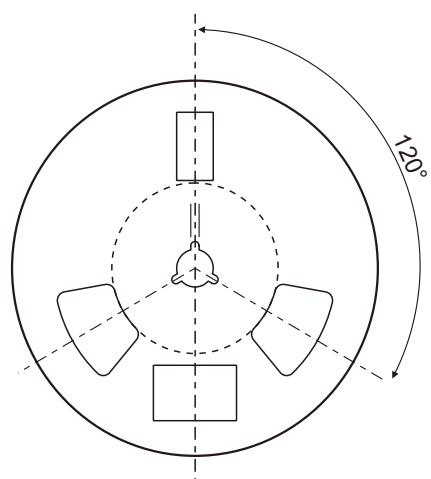
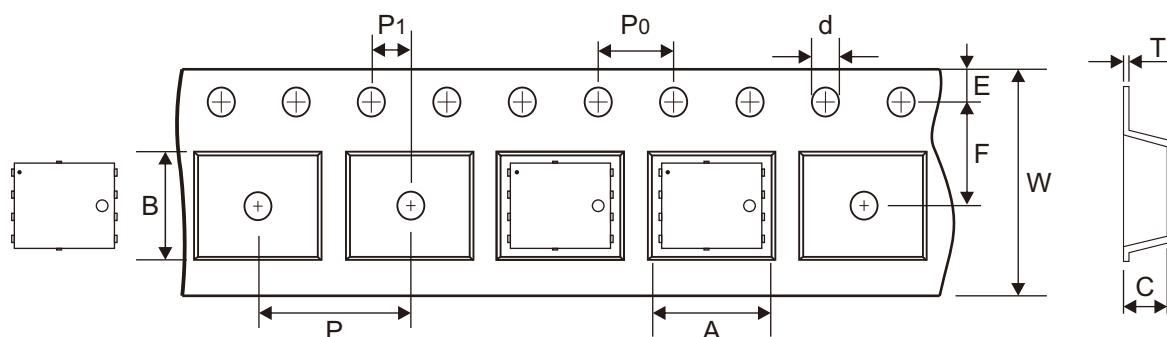


## Typical Rating and Characteristic Curves (ACMS93P04H8-HF)

Fig.13 - Safe Operation Area



## Reel Taping Specification

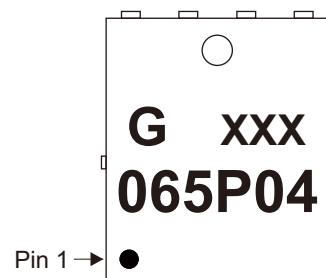


PDFN5x6 -8L	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	$6.30 \pm 0.10$	$5.30 \pm 0.10$	$1.20 \pm 0.10$	$1.55 + 0.01 - 0.00$	$330.00 \pm 2.00$	$100.00 \pm 2.00$	$13.00 \pm 0.20$
	(inch)	$0.248 \pm 0.004$	$0.209 \pm 0.004$	$0.047 \pm 0.004$	$0.061 + 0.0004 - 0.0000$	$12.992 \pm 0.079$	$3.937 \pm 0.079$	$0.512 \pm 0.008$

PDFN5x6 -8L	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	$1.75 \pm 0.10$	$5.50 \pm 0.10$	$8.00 \pm 0.10$	$4.00 \pm 0.10$	$2.00 \pm 0.05$	$0.25 \pm 0.03$	$12.00 + 0.30 - 0.10$	$18.50 \pm 2.00$
	(inch)	$0.069 \pm 0.004$	$0.217 \pm 0.004$	$0.315 \pm 0.004$	$0.157 \pm 0.004$	$0.079 \pm 0.002$	$0.010 \pm 0.001$	$0.472 + 0.012 - 0.004$	$0.728 \pm 0.079$

## Marking Code

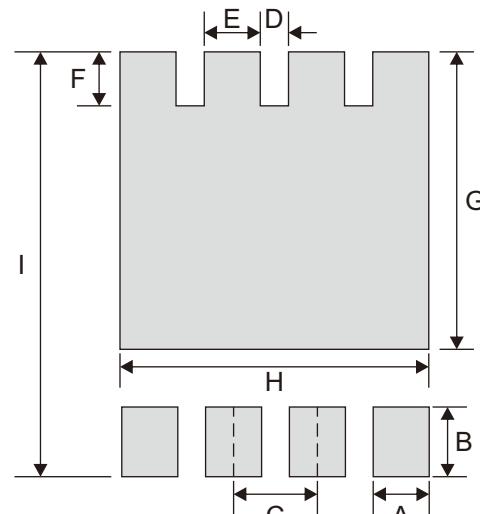
Part Number	Marking Code
ACMS93P04H8-HF	065P04



XXX = Control code

## Suggested P.C.B. PAD Layout

SIZE	PDFN5x6-8L	
	(mm)	(inch)
A	0.80	0.031
B	1.00	0.039
C	1.27	0.050
D	0.47	0.019
E	0.80	0.031
F	0.85	0.033
G	4.50	0.177
H	4.61	0.181
I	6.40	0.252



## Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
PDFN5x6-8L	5,000	13